

ABSTRACT

There is provided a plasma etching method capable of selectively etching an etching object containing oxide of at least one of tin and indium compared to a non-etching object. The plasma etching method includes: an etching step of bringing an etching gas containing an unsaturated compound having a fluorine atom and a bromine atom in the molecule thereof into contact with a member to be etched including an etching object to be etched by the etching gas and a non-etching object not to be etched by the etching gas in the presence of plasma, performing etching while applying a bias power exceeding 0 W to a lower electrode supporting the member to be etched, and selectively etching the etching object compared to the non-etching object. The etching object contains oxide of at least one of tin and indium and the non-etching object contains at least one of a silicon-containing compound and a photoresist.

Fig. 1